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**ATTENTION: BOX AFTER FINAL
RESPONSE UNDER 37 C.F.R. § 1.116
EXPEDITED PROCEDURE REQUESTED
EXAMINING GROUP 2814**

Customer No. 22,852
Attorney Docket No. 08245.0027

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Jun Dong KIM et al.

Serial No.: 09/892,878

Filed: June 28, 2001

For: METHOD FOR FORMING GATE
ELECTRODES IN A
SEMICONDUCTOR DEVICE
USING FORMED FINE
PATTERNS

Commissioner for Patents and Trademarks
Washington, DC 20231

Sir:

AMENDMENT AFTER-FINAL AND REQUEST FOR RECONSIDERATION

In response to the Final Office Action dated December 3, 2002, and pursuant to
37 C.F.R. § 1.116, Applicants propose that this application be amended as follows:

IN THE CLAIMS:

Please amend claims 6 and 8 as indicated in the attached Appendix and as
presented below:

6. (Amended) A method for forming fine patterns of a semiconductor device,
the method comprising:
forming a patterning layer over a semiconductor wafer;

#9A Just
M. Bauman
9/6/02

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ma'sha
5/13/03

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FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

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